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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

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Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







Revision. 2

Panasonic

MOS FET

SK830321KL

SK830321KL

Silicon N-channel MOS FET

For Load-switching / For DC-DC Converter

■ Features

- Low Drain-source On-state Resistance:RDS(on)typ = 24 m Ω (VGS = 4.5 V)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: 21

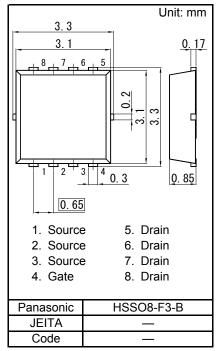
■ Packaging

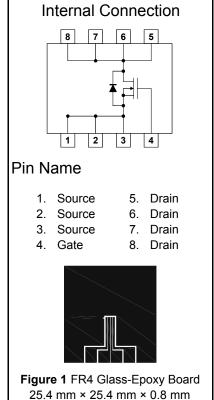
Embossed type (Thermo-compression sealing): 5 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter			Symbol	Rating	Unit		
Drain to Source Voltage			VDS	30	V		
Gate to Source Voltage			VGS	±20	V		
Drain Current	Ta=25 °C, t =10 s *1		ID	9			
	Ta=25 °C, DC ^{*1}			7	Α		
Dialii Cuilelli	Tc=25 °C			18			
	Pulsed	d, Tch<150 °C ^{*2}		27			
Total Power		Ta=25 °C, DC *1	PD	2	W		
Dissipation		Tc=25 °C	FD	13	VV		
Thermal Resistance		Channel to Ambient	Rth(ch-a)	62.5	°C / W		
memai Kesisi	ance	Channel to Case	Rth(ch-c)	9.2	C / VV		
Channel Temperature			Tch	150			
Operating ambient temperature			Topr	-40 to +85	°C		
Storage Temperature Range			Tstg	-55 to +150			
Avalanche Current (Single pulse) *3			IAR	4.5	Α		
Avalanche Energy (Single pulse) *3		EAR	2.5	mJ			

- Note *1 Device mounted on a glass-epoxy board in Figure 1
 - *2 Pulse test: Ensure that the channel temperature does not exceed 150 °C
 - *3 VDD = 24 V, VGS = 10 to 0 V, L = 0.1 mH, Tch = 25 $^{\circ}$ C (initial)





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■ Electrical Characteristics Ta = 25 °C ± 3 °C

Static Characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1.0 mA, VGS = 0 V	30			V
Zero Gate Voltage Drain Current	IDSS	VDS = 30 V, VGS = 0 V			10	μΑ
Gate-source Leakage Current	IGSS	VGS = ±16 V, VDS = 0 V			±10	μΑ
Gate-source Threshold Voltage	Vth	ID = 519 μA, VDS = 10 V	1.3		3	V
Drain-source On-state Resistance	RDS(on)1	ID = 4.5 A, VGS = 10 V		17	24	mΩ
Diain-source Oil-state Nesistance	RDS(on)2	ID = 4.5 A, VGS = 4.5 V		24	30	

Dynamic Characteristics

Byriamio enaracteriotico	10 11	0 1111	T a 4:	-		
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input Capacitance	Ciss	VDS = 10 V, VGS = 0 V,		470	658	
Output Capacitance	Coss	f = 1 MHz		69	97	pF
Reverse Transfer Capacitance	Crss	1 = 1 MH2		38	61	
Turn-on Delay Time *1	td(on)	VDD = 15 V, VGS = 0 to 10 V		4		ns
Rise Time *1	tr	ID = 4.5 A		3		115
Turn-off Delay Time *1	td(off)	VDD = 15 V, VGS = 10 to 0 V		31		ne
Fall Time *1	tf	ID = 4.5 A		5		ns
Total Gate Charge	Qg	VDD = 15 V VCS = 0 to 4 5 V		3.9		
Gate to Source Charge	Qgs	VDD = 15 V, VGS = 0 to 4.5 V ID = 4.5 A		1.4		nC
Gate to Drain Charge	Qgd	10 - 4.5 A		1.7		
Gate Resistance	rg	f = 5 MHz		1.9	3	Ω

Body Diode Characteristic

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Diode Forward Voltage	VSD	IS = 4.5 A, VGS = 0 V		0.8	1.2	V

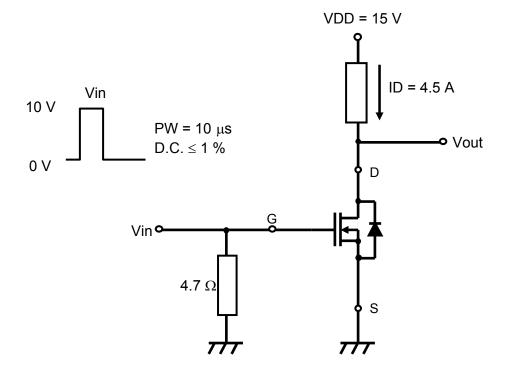
Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

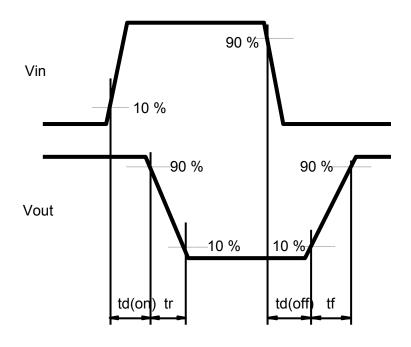
^{2. *1} Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

MOS FET

SK830321KL

*1 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time



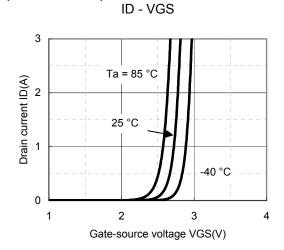


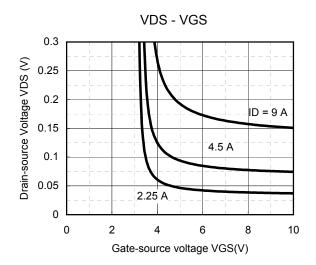
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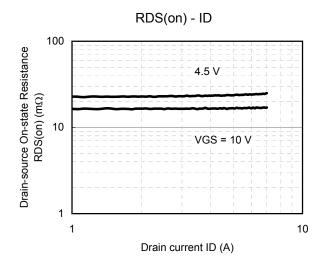
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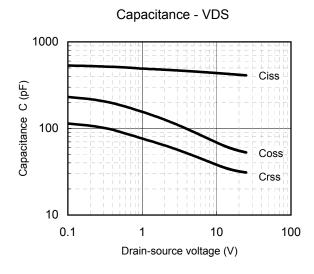
Technical Data (reference)

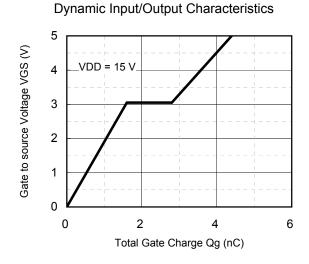
ID - VDS 6 10 V Drain current ID (A) 3.5 V VGS = 3 V 0.1 0.2 0.3 0 Drain-source voltage VDS(V)







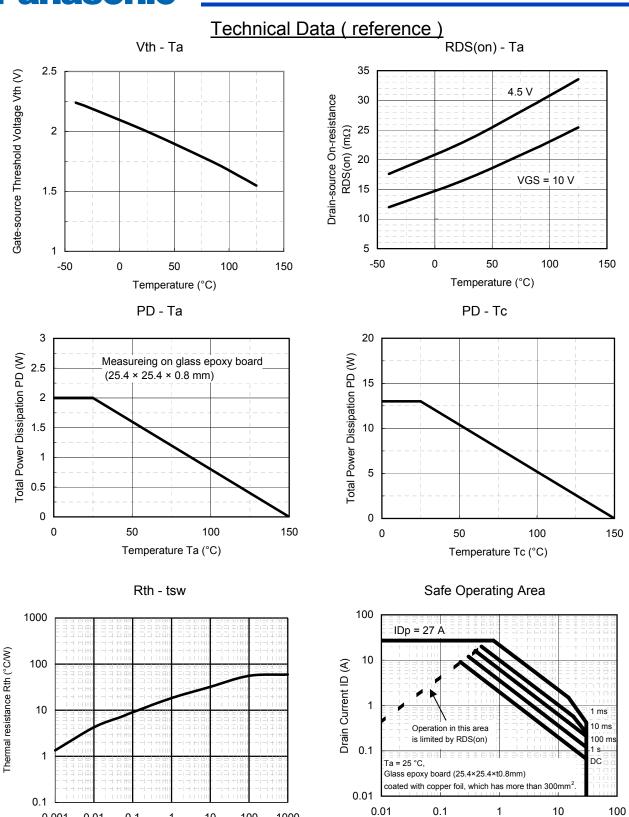




Established: 2012-12-19

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Drain-source voltage VDS (V)

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0.001

0.01

0.1

1

Pulse Width tsw (s)

10

100

1000

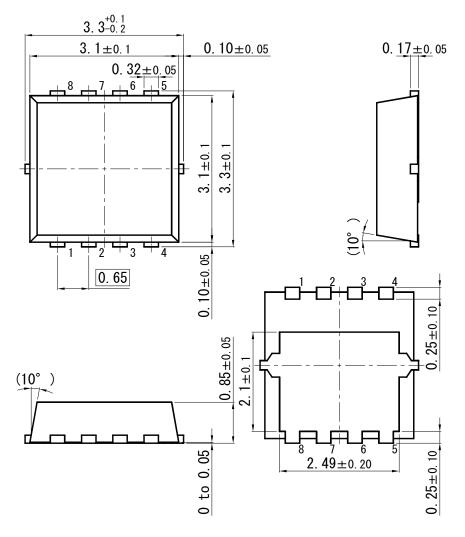
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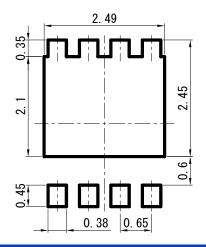
HSSO8-F3-B

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Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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